



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/816,927	03/23/2001	Franz Auerbach	GR 98 P 2551/P	6167

7590 07/31/2002

LERNER AND GREENBERG, P.A.
Post Office Box 2480
Hollywood, FL 33022-2480

EXAMINER

ROSE, KIESHA L

ART UNIT

PAPER NUMBER

2822

DATE MAILED: 07/31/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/816,927

Applicant(s)

AUERBACH ET AL. *ne*

Examiner

Kiesha L. Rose

Art Unit

2822

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 06 May 2002.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-20 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action:
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other:

DETAILED ACTION

This Office Action is in response to the amendment filed 6 May 2002.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 12-20 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claims 12-20 disclose semiconductor regions to surround the semiconductor zones at a respective distance "except for a channel". It is unclear if the semiconductor region does not surround the channel or if the channel does not surround the semiconductor region at the respective distance.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-3, 5-7, 10, 12-14, 16-17 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nishizawa et al. (U.S. Patent 5,175,598) in view of Stengl (U.S. Patent 5,113,237).

Art Unit: 2822

Nishizawa discloses a semiconductor-switching device (Fig. 2) that contains a semiconductor body (4,5) of first conductivity type N having a first and second surface which are opposite to each other, a first electrode (2') formed on the first surface, a second electrode (5') formed on the second surface, a semiconductor zone (2) of second conductivity type P, where a PN junction is formed between, and is in contact with the first electrode (2'), an injector disposed in a surface of the semiconductor body (4,5), semiconductor regions (3) of second conductivity type P with a second doping concentration provided in the semiconductor body (4,5) that are disposed at a respective distance from the semiconductor zone (2) so that the semiconductor regions (3) surround the semiconductor zone (2) in a well shape, semiconductor regions (3) that are interrupted by channels formed in the semiconductor body (4,5) at a plurality of locations for increasing voltage where the channels are configured such that electric field spikes are avoided when a reverse voltage is applied between the first and second electrodes and an insulating zone (6) formed on the semiconductor body (4,5) that shields charge carriers. Nishizawa discloses all of the limitations except for the semiconductor body having a doping concentration greater than 5×10^{13} charge carrier cm^{-3} . Whereas Stengl discloses a semiconductor device (Fig. 1) that contains a semiconductor body (1) with a doping concentration of 10^{18} cm^{-3} . Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the switching device of Nishizawa by incorporating the semiconductor body to have a doping concentration of 10^{18} cm^{-3} to properly form a conductive region in a semiconductor layer as taught by Stengl.

Art Unit: 2822

Claims 4 and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nishizawa et al. and Stengl as applied to claim 1 above, and further in view of Siergiej et al. (U.S. Patent 5,945,701).

Nishizawa and Stengl disclose all of the limitations except for the semiconductor body having a drift region. Whereas Siergiej discloses a static induction transistor (Fig. 12) that contains a semiconductor body, which contains a drift region (38) and channel regions (36) formed in drift region. The drift region is formed so that the charge carriers can flow from one region to the other. (Column 3, lines 27-31) Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the semiconductor devices of Nishizawa and Stengl by incorporating a drift region in the semiconductor body, which will allow for the charge carriers to flow from one region to the other as taught by Siergiej.

Claims 8, 9, 18 and 19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nishizawa et al. and Stengl as applied to claim 1 above, and further in view of Notley (U.S. Patent 5,324,971).

Nishizawa and Stengl disclose all of the limitations except for the semiconductor body to contain field plates and guard rings. Whereas Notley discloses a semiconductor device (Fig. 4) that contains a semiconductor body (2) that has field plates (20) formed on a surface of the semiconductor body. The field plates are formed on a major surface of the semiconductor body to cause electric fields to spread laterally outward across the active area to increase the breakdown voltage of the semiconductor device. (Abstract) The semiconductor body also contains a guard ring (12) that

Art Unit: 2822

surrounds the edge of the semiconductor body. The guard ring is formed to influence the voltage at the field plate areas. (Column 5, lines 15-24) Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the semiconductor devices of Nishizawa and Stengl by incorporating field plates and guard rings to increase the breakdown voltage of the semiconductor device as taught by Notley.

Claim 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nishizawa et al. in view of Stengl.

Nishizawa discloses a semiconductor switching device (Fig. 2) that contains a transistor comprising a semiconductor body (4,5) of first conductivity type N having a first and second surface which are opposite to each other, a first electrode (2') formed on the first surface, a second electrode (5') formed on second surface, a semiconductor zone (2) of second conductivity type P where a PN junction is formed between and is in contact with the first electrode (2'), semiconductor regions (3) of second conductivity type P with a second doping concentration provided in the semiconductor body (4,5) that are disposed at a respective distance from the semiconductor zone (2) so that the semiconductor regions (3) surround the semiconductor zone (2), semiconductor regions (3) that are interrupted by channels formed in the edge region in the semiconductor body (4,5) at a plurality of locations for increasing voltage where the channels are configured such that electric field spikes are avoided when a reverse voltage is applied between the first and second electrodes and an insulating zone (6) formed on semiconductor body (4,5) that shields charge carriers. Nishizawa discloses all of the

Art Unit: 2822

limitations except for the semiconductor body to have a doping concentration greater than 5×10^{13} charge carrier cm^{-3} . Whereas Stengl discloses a semiconductor device (Fig. 1) that contains a semiconductor body (1) with a doping concentration of 10^{18} cm^{-3} . Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the switching device of Nishizawa by incorporating the semiconductor body to have a doping concentration of 10^{18} cm^{-3} to properly form a conductive region in a semiconductor layer as taught by Stengl.

Response to Arguments

Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any

Art Unit: 2822

extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kiesha L. Rose whose telephone number is 703-605-4212. The examiner can normally be reached on M-F 8:30-6:00 off 1st Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr. can be reached on 703-308-4940. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

KR
KLR

July 24, 2002



CARL WHITEHEAD, JR.
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800